

# 1.27mm Silicon PD Chip datasheet

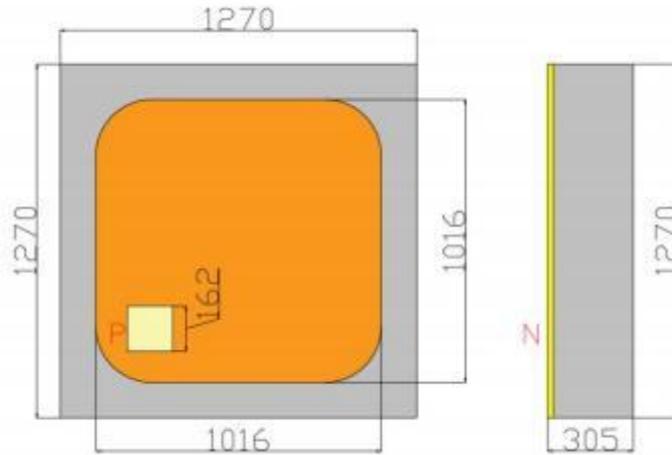
P/N : WS9D-01C

## Application

Si PIN photodiode chip

## Structure

Planar type : PIN diode  
 Electrodes :  
 Back side ( Cathode ) : Au  
 Top side ( Anode ) : Al



## DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	1016 x 1016 ± 20			μm
Chip width	1270			μm
Chip length	1270			μm
Chip height	290	305	320	μm
Pad Area	162			μm

## Electro-Optical Characteristics ( @ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H=0	0.5		1.3	V
Reverse Voltage	Vbr	Ir=100μA, H=0	35			V
Reverse Dark Current	Id	Vr=10V			10	nA
Sensitive Wavelength Range	λ		400	940	1100	nm
Capacitance	Cj	VR=3V, f=1MHz		11		pF